

DSS5160FDB

60V DUAL PNP LOW VCE(sat) TRANSISTOR

Features

- BV_{CEO} > -60V
- I_C = -1A high Continuous Collector Current
- $R_{CE(sat)} = 200 m\Omega$ for a Low Equivalent On-Resistance
- Low Saturation Voltage V_{CE(sat)} < 340mV @ 1A
- P_D up to 2.47W for power demanding applications
- R_{θJA} efficient, 40% lower than SOT26
- Low profile 0.6mm high package for thin applications
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

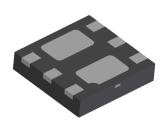
Mechanical Data

- Case: U-DFN2020-6
- Case Material: Molded Plastic. "Green" Molding Compound.
- UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu, Solderable per MIL-STD-202, Method 208 (24)
- Weight: 0.0065 grams (Approximate)

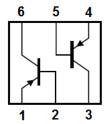
Application

- Load Switch
- Power Management
- Charging Circuits
- Power Switches (e.g. Motors, Fans)

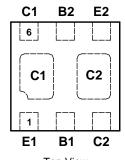
U-DFN2020-6



Bottom View



Device Symbol



Top View Pin-Out

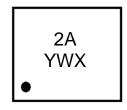
Ordering Information (Notes 4)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
DSS5160FDB-7	2A	7	8	3,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



2A = Product type Marking Code

Y = Year: 0~9

W = Week: A~Z: 1~26 week;

a~z; 27~52 week; z represents

52 and 53 week $X = A \sim Z$: Internal code



Absolute Maximum Ratings - Q1 & Q2 (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-60	V
Collector-Emitter Voltage	V_{CEO}	-60	V
Emitter-Base Voltage	V_{EBO}	-7	V
Continuous Collector Current	Ic	-1	Α
Peak Pulse Collector Current	I _{CM}	-1.5	A
Base Current	I _B	-300	mA
Peak Base Current	I _{BM}	-1	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
	(Notes 5 & 7)		405	mW	
Power Dissipation	(Notes 5 & 8)	D .	510		
Power Dissipation	(Notes 6 & 7)	P_D	1650		
	(Notes 6 & 8)		2470		
	(Notes 5 & 7)		308	°C/W	
Thermal Resistance, Junction to Ambient	(Notes 5 & 8)	В	245		
Thermal Resistance, Junction to Ambient	(Notes 6 & 7)	$R_{\theta JA}$	76		
	(Notes 6 & 8)		51		
Thermal Resistance, Junction to Lead	(Note 9)	$R_{\scriptscriptstyle{ hetaJL}}$	18	°C/W	
Operating and Storage Temperature Range		T_{J}, T_{STG}	-55 to +150	°C	

ESD Ratings (Note 10)

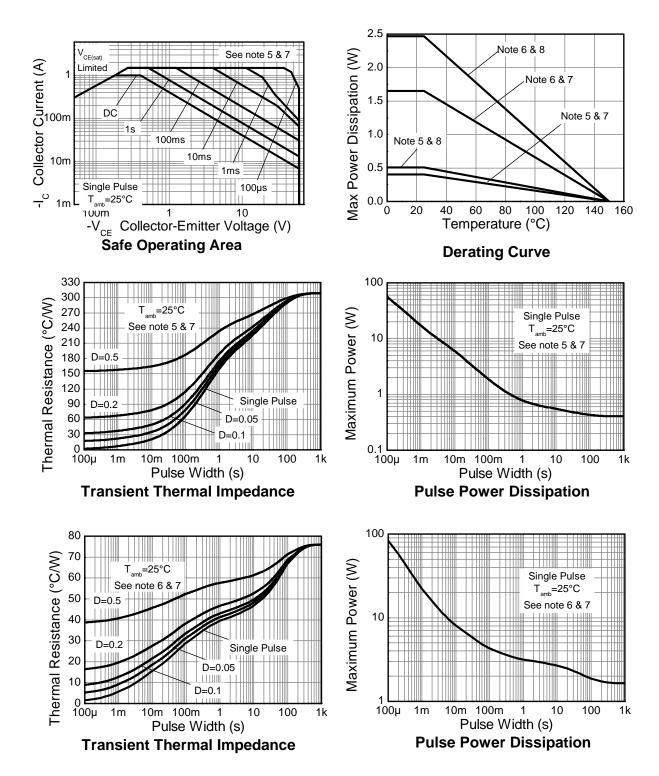
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge – Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge – Machine Model	ESD MM	400	V	С

Notes:

- 5. For a device mounted with the exposed collector pads on minimum recommended pad layout that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
- 6. Same as note (5), except the device is mounted with the collector pad on 28mm x 28mm (8cm²) 2oz copper.
- 7. For a dual device with one active die.
- 8. For dual device with 2 active die running at equal power.
- 9. Thermal resistance from junction to solder-point (on the exposed collector pads).
- 10. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



Thermal Characteristics and Derating Information





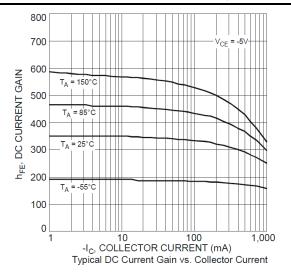
Electrical Characteristics – Q1 & Q2 (@T_A = +25°C, unless otherwise specified.)

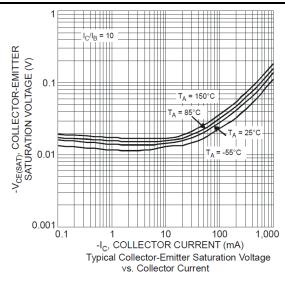
Characteristic	Symbol	Min	Тур	Max	Unit	Test Conditions
Collector-Base Breakdown Voltage		-60	_	_	V	$I_{C} = -100 \mu A$
Collector-Emitter Breakdown Voltage (Note 11)		-60	_	_	V	$I_C = -10mA$
Emitter-Base Breakdown Voltage	BV _{EBO}	-7	_		V	$I_E = -100 \mu A$
Collector-Base Cutoff Current	-		_	-100	nA	$V_{CB} = -48V, I_{E} = 0$
	Ісво		_	-50	μΑ	$V_{CB} = -48V$, $I_E = 0$, $T_A = +150$ °C
Emitter-Base Cutoff Current	I _{EBO}		_	-100	nA	$V_{EB} = -5.6V, I_{C} = 0$
		170	_	_		$V_{CE} = -2V, I_{C} = -100mA$
DC Current Gain (Note 11)	h _{FE}	120	_	_	_	$V_{CE} = -2V, I_{C} = -500mA$
		70	_			V _{CE} = -2V, I _C = -1A
		_	_	-180		$I_C = -500 \text{mA}, I_B = -50 \text{mA}$
Collector-Emitter Saturation Voltage (Note 11)	V _{CE(sat)}		_	-340	mV	$I_C = -1A$, $I_B = -100mA$
	(3.37)	_	_	-550		$I_C = -1A$, $I_B = -50mA$
Equivalent On-Resistance (Note 11)	R _{CE(sat)}	_	_	360	mΩ	$I_E = -0.5A, I_B = -50mA$
		_	_	-1		$I_C = -0.5A$, $I_B = -50mA$
Base-Emitter Saturation Voltage (Note 11)	V _{BE(sat)}	_	_	-1.0	V	$I_C = -1A$, $I_B = -50mA$
	, ,		_	-1.1		I _C = -1A, I _B = -100mA
Base-Emitter Turn-on Voltage (Note 11)	V _{BE(on)}	_	_	-0.9	V	$V_{CE} = -2V, I_{C} = -0.5A$
Transition Frequency	f _T	65	_	_	MHz	$V_{CE} = -10V, I_{C} = -50mA,$ f = 100MHz
Output Capacitance	C _{obo}	_	_	15	pF	V _{CB} = -10V, f = 1MHz
Turn-On Time	t _{on}	_	75	_	ns	
Delay Time	t _d	_	35	_	ns	ĺ
Rise Time	t _r		40	_	ns	Vcc = -10V. Ic = -0.5A.
Turn-Off Time		_	265	_	ns	$I_{B1} = -I_{B2} = 25\text{mA}$
Storage Time	ts	_	230	_	ns	
Fall Time	t _f	_	35	_	ns	

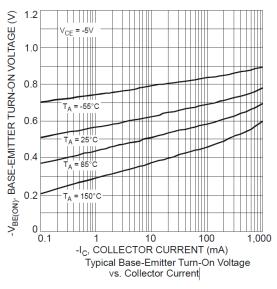
Note: 11. Measured under pulsed conditions. Pulse width $\leq 300 \mu s$. Duty cycle $\leq 2\%$.

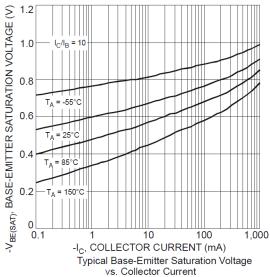


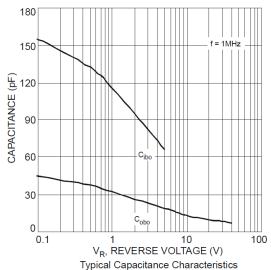
Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)







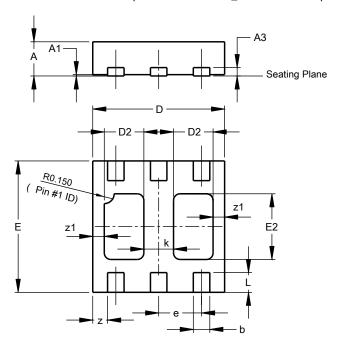






Package Outline Dimensions

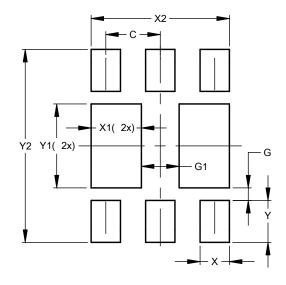
Please see AP02001 at http://www.diodes.com/_files/datasheets/ap02001.pdf for the latest version.



U-DFN2020-6 Type B					
Dim			Тур		
Α	0.545	0.605	0.575		
A1	0.00	0.05	0.02		
А3	-	-	0.13		
b	0.20	0.30	0.25		
D	1.95	2.075	2.00		
D2	0.50	0.70	0.60		
е	-	-	0.65		
Е	1.95	2.075	2.00		
E2	0.90	1.10	1.00		
k	-	-	0.45		
L	0.25	0.35	0.30		
Z	-	-	0.225		
z 1	-	-	0.175		
All Dimensions in mm					

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/_files/datasheets/ap02001.pdf for the latest version.



Dimensions	Value		
Dillicitatoria	(in mm)		
С	0.650		
G	0.150		
G1	0.450		
Х	0.350		
X1	0.600		
X2	1.650		
Y	0.500		
Y1	1.000		
Y2	2.300		



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